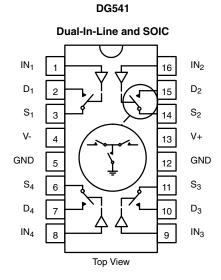
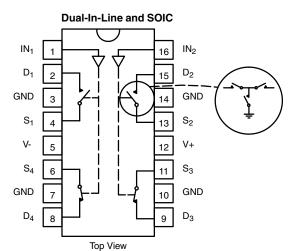
### Vishay Siliconix







**VISHAY** 

TRUTH TABLE - DG541					
Logic	Switch				
0	OFF				
1	ON				
Logic "0" ≤ 0.8 V					

 Logic
 SW1, SW2
 SW3, SW4

 0
 OFF
 ON

 1
 ON
 OFF

 Logic "0" ≤ 0.8 V
 V

Logic "1" ≥ 2 V

ORDERING INFORMATION					
Temp Range	Package	Part Number			
DG540	·				
- 40 to 85 °C	20-Pin Plastic DIP	DG540DJ-E3			
- 40 10 65 0	20-Pin PLCC	DG540DN-E3			
- 55 to 125 °C	00 Din Sidebraza	DG540AP			
- 55 10 125 10	20-Pin Sidebraze	DG540AP/883			
DG541					
- 40 to 85 °C	16-Pin Plastic DIP	DG541DJ-E3			
- 40 10 65 0	16-Pin Narrow SOIC	DG541DY-T1-E3			
- 55 to 125 °C	16-Pin Sidebraze	DG541AP			
- 55 10 125 10	To-Pill Sidebraze	DG541AP/883, 5962-9076401MEA			
DG542					
10 to 95 °C	16-Pin Plastic DIP	DG542DJ-E3			
- 40 to 85 °C	16-Pin Narrow SOIC	DG542DY-T1-E3			
- 55 to 125 °C	16-Pin Sidebraze	DG542AP			
- 55 10 125 0	TO-FITI SIDEDIAZE	DG542AP/883, 5962-91555201MEA			

DG542

Logic "1"  $\ge$  2 V



### Vishay Siliconix

	Parameter	Symbol	Limit	Unit
V+ to V-			- 0.3 to 21	
V+ to GND			- 0.3 to 21	
V- to GND			- 19 to + 0.3	
Digital Inputs			(V-) - 0.3 to (V+) + 0.3 or 20 mA, whichever occurs first	V
V <sub>S</sub> , V <sub>D</sub>			(V-) - 0.3 to (V+) + 14 or 20 mA, whichever occurs first	
Continuous Current (Any Terminal)			20	mA
Current, S or D (Pulsed at 1 ms	s, 10 % duty cycle max)		40	ША
Storage Temperature	(AP Suffix)		- 65 to 150	°C
Storage Temperature	(DJ, DN, DY Suffixes)		- 65 to 125	C
	16-Pin Plastic DIP <sup>b</sup>		470	
Power Dissipation (Package) <sup>a</sup>	20-Pin Plastic DIP <sup>c</sup>		800	
	16-Pin Narrow Body SOIC <sup>d</sup>		640	mW
	20-Pin PLCC <sup>d</sup>		800	
	16-, 20-Pin Sidebraze DIP <sup>e</sup>		900	

Notes:

a. All leads welded or soldered to PC Board.

b. Derate 6.5 mW/°C above 25 °C.

c. Derate 7 mW/°C above 25 °C.

d. Derate 10 mW/°C above 75 °C.

e. Derate 12 mW/°C above 75 °C.

#### SCHEMATIC DIAGRAM (typical channel)

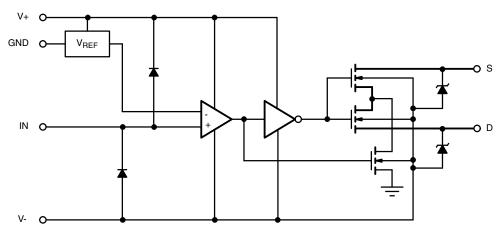


Figure 1.

### Vishay Siliconix



$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	<b>SPECIFICATIONS</b> <sup>a</sup>										
$\begin{array}{ c c c c c c c c c c c c c c c c c c c$			Unless Specifie	ed							
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $					h		4		F	F	
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $		Symbol	$V_{\rm INH} = 2$ V, $V_{\rm INL} = 0$	).8 V'	Temp. <sup>D</sup>	Тур. <sup>с</sup>	Min.ª	Max. <sup>a</sup>	Min. <sup>a</sup>	Max. <sup>a</sup>	Unit
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	÷	1	Γ		1	I		l	1	1	
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $		V <sub>ANALOG</sub>	V- = - 5 V, V+ =	12	-		- 5	-	- 5	-	V
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	On-Resistance		I <sub>S</sub> = - 10 mA, V <sub>D</sub> =	= 0 V				100		75	Ω
	R <sub>DS(on)</sub> Match	$\Delta R_{DS(on)}$			Room	2		-		-	
$\begin{array}{ c c c c c c c c c c c c c c c c c c c$	Source Off Leakage Current	I <sub>S(off)</sub>	$V_{\rm S} = 0  \rm V,  V_{\rm D} = 10$	0 V		- 0.05	- 500	500	- 100	100	
$\begin{array}{ c c c c c c c c c c c c c c c c c c c$	Drain Off Leakage Current	I <sub>D(off)</sub>	$V_{\rm S} = 10 \ {\rm V}, \ {\rm V}_{\rm D} = 0$	0 V	Full	- 0.05	- 500	500	- 100	100	nA
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Channel On Leakage Current	I <sub>D(on)</sub>	$V_{S} = V_{D} = 0 V$	,		- 0.05					
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	Digital Control										
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	Input Voltage High				Full		2		2		v
$\begin{array}{ c c c c c c c c c c c c c c c c c c c$	Input Voltage Low	V <sub>INL</sub>			Full			0.8		0.8	v
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Input Current	I <sub>IN</sub>	V <sub>IN</sub> = GND or V	<b>'</b> +		0.05					μA
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Dynamic Characteristics										
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	On State Input Capacitance <sup>e</sup>	C <sub>S(on)</sub>	$V_{\rm S} = V_{\rm D} = 0 V$	,	Room	14		20		20	
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Off State Input Capacitance <sup>e</sup>		V <sub>S</sub> = 0 V		Room	2		4		4	pF
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Off State Output Capacitance <sup>e</sup>	C <sub>D(off)</sub>	V <sub>D</sub> = 0 V		Room	2		4		4	1
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Bandwidth		$R_L = 50 \Omega$ , See Fig	gure 5	Room	500					MHz
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	Turn On Time	<b>t</b>				45				-	
$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	ium-on nine	LON	_	DG542		55					ne
$\begin{array}{ c c c c c c c c c c c c c c c c c c c$		torr				20					115
$\begin{array}{c c c c c c c c c c c c c c c c c c c $		OFF				25					
Off IsolationOIRRImage: General conditionDGS Hz f = 5 MHz DG541DG541Room Room- 60Image: General conditionMage: General conditionGeneral conditionGeneral conditionMage: General condition <td>Charge Injection</td> <td>Q</td> <td></td> <td>= 0 V</td> <td>Room</td> <td>- 25</td> <td></td> <td></td> <td></td> <td></td> <td>рС</td>	Charge Injection	Q		= 0 V	Room	- 25					рС
See Figure 4DG542Room- 75Image: Constant of the set of th			$R_{IN} = 75 \Omega, R_L = 75 \Omega$	DG540	Room	- 80					
All Hostile Crosstalk $X_{TALK(AH)}$ $R_{IN} = 10 \Omega, R_L = 75 \Omega$ f = 5 MHz, See Figure 6       Room       - 85       Image: Constraint of the second se	Off Isolation	OIRR	f = 5 MHz		Room	- 60					
All Hostile Crosstalk $\Lambda_{TALK(AH)}$ $f = 5$ MHz, See Figure 6     Hoom $-85$ Image: Constraint of the second se			See Figure 4	DG542	Room	- 75					dB
Positive Supply Current     I+       All Channels On or Off     Room     3.5     6     6       Full     Boom     - 3.2     - 6     - 6	All Hostile Crosstalk	X <sub>TALK(AH)</sub>			Room	- 85					
Positive Supply Current         I+         All Channels On or Off         Full         9         9         9         mA           Negative Supply Current         I-         All Channels On or Off         Room         - 3.2         - 6         - 6         mA	Power Supplies		·								
Negative Supply Current	Positive Supply Current	l+	All Channels On a	r Off		3.5					m A
	Negative Supply Current	I-		All Channels On or Off		- 3.2					

Notes:

a. Refer to PROCESS OPTION FLOWCHART .

b. Room = 25  $^{\circ}\text{C},$  full = as determined by the operating temperature suffix.

c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.

d. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.

e. Guaranteed by design, not subject to production test.

f.  $V_{IN}$  = input voltage to perform proper function.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

www.vishay.com 4 Document Number: 70055 S11-1429–Rev. H, 18-Jul-11



### DG540, DG541, DG542 Vishay Siliconix

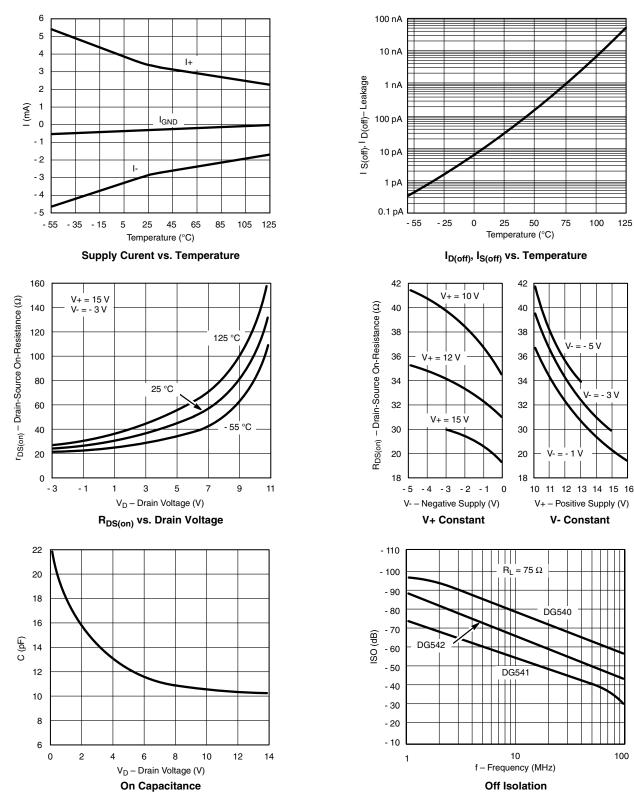
100

= - 5 V v.

V- = - 3 V

125

### **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



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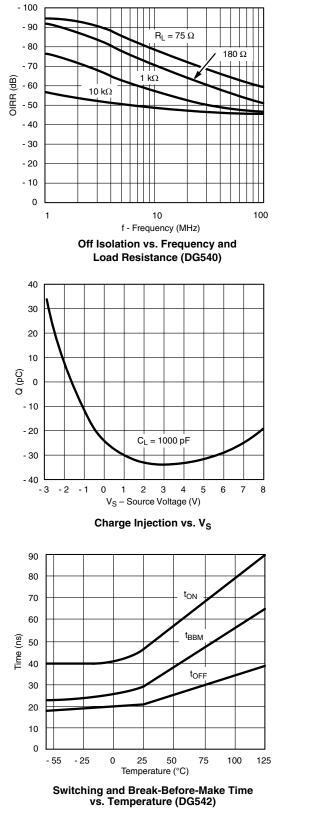
100

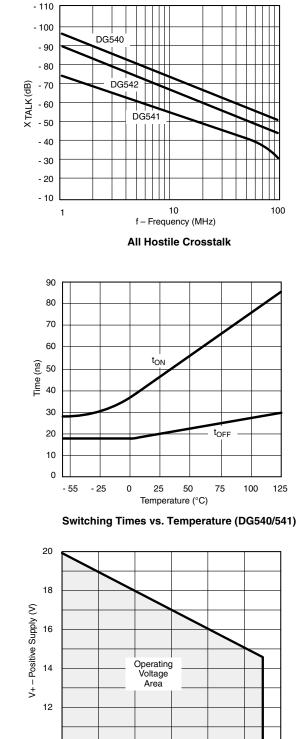
5

Vishay Siliconix



#### **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)





Operating Supply Voltage Range

- 4

- 5

- 3

V- - Negative Supply (V)

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- 6

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10

0

- 1

- 2

Figure 5. Bandwidth

#### + 15 V С V+ Vo D s ٧s റ $\sim$ Rg $= 75 \Omega$ R<sub>L</sub> 75 Ω ξ IN 0 V, 2.4 V 0 GND V. С Q - 3 V $V_{S}$ Off Isolation = 20 log Vo C = RF Bypass Figure 4. Off Isolation

 $\Delta V_O$  = measured voltage error due to charge injection The charge injection in coulombs is  $\Delta Q = C_L \times DV_Q$ 

+ 15 V

V.

Ò

- 3 V

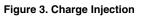
D

Q

V+

OFF

 $\Delta V_{O}$ 





٧<sub>0</sub>

 $\mathsf{IN}_{\mathsf{X}}$ 

C

 $R_g = 50 \ \Omega$ 

0 V, 2.4 V O

s

IN

GND

ON

#### **TEST CIRCUITS**

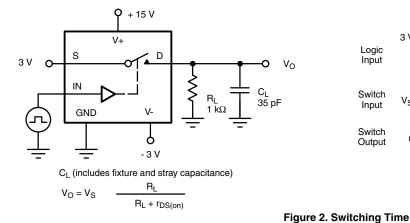
Rg

3 V

л

Vg

VISHAY



+ 15 V

D ٠.

V-

δ - 3 V 0 Vo

C<sub>L</sub> 1000 pF

V+

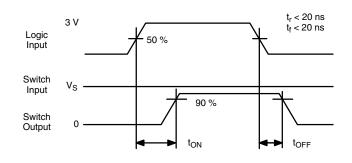
 $\sim$ 

s

IN

GND

\_



# DG540, DG541, DG542

Vishay Siliconix

ON

 $V_{O}$ 

0

R<sub>L</sub> 50 Ω

Ş

С

**Vishay Siliconix** 

#### **TEST CIRCUITS**

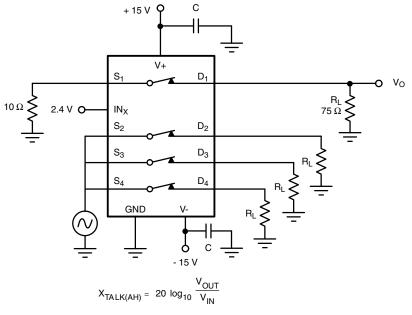


Figure 6. All Hostile Crosstalk

#### APPLICATIONS

#### **Device Description**

The DG540, DG541, DG542 family of wideband switches offers true bidirectional switching of high frequency analog or digital signals with minimum signal crosstalk, low insertion loss, and negligible non-linearity distortion and group delay. Built on the Siliconix D/CMOS process, these "T" switches provide excellent off-isolation with a bandwidth of around 500 MHz (350 MHz for DG541). Silicon-gate D/CMOS processing also yields fast switching speeds.

An on-chip regulator circuit maintains TTL input compatibility over the whole operating supply voltage range, easing control logic interfacing.

Circuit layout is facilitated by the interchangeability of source and drain terminals.

#### **Frequency Response**

A single switch on-channel exhibits both resistance ( $R_{DS(on)}$ ) and capacitance ( $C_{S(on)}$ ). This RC combination has an attenuation effect on the analog signal – which is frequency dependent (like an RC low-pass filter). The - 3-dB bandwidth of the DG540 is typically 500 MHz (into 50  $\Omega$ ). This measured figure of 500 MHz illustrates that the switch channel can not be represented by a two stage RC combination. The on capacitance of the channel is distributed along the on-resistance, and hence becomes a more complex multi stage network of R's and C's making up the total  $R_{DS(on)}$  and  $C_{S(on)}$ . See Application Note AN502 for more details.

#### **Off-Isolation and Crosstalk**

Off-isolation and crosstalk are affected by the load resistance and parasitic inter-electrode capacitances. Higher off-isolation is achieved with lower values of  $R_L$ . However, low values of  $R_L$  increase insertion loss requiring gain adjustments down the line. Stray capacitances, even a fraction of 1 pF, can cause a large crosstalk increase. Good layout and ground shielding techniques can considerably improve your ac circuit performance.



#### **APPLICATIONS**

#### **Power Supplies**

A useful feature of the DG54X family is its power supply flexibility. It can be operated from a single positive supply (V+) if required (V- connected to ground).

Note that the analog signal must not exceed V- by more than - 0.3 V to prevent forward biasing the substrate p-n junction. The use of a V- supply has a number of advantages:

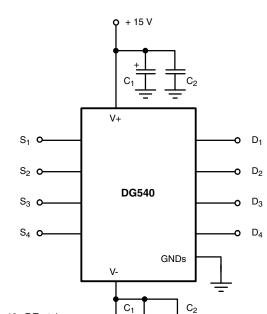
- 1. It allows flexibility in analog signal handling, i.e., with V- = -5 V and V+ = 12 V; up to  $\pm$  5 V ac signals can be controlled.
- 2. The value of on capacitance  $[C_{S(on)}]$  may be reduced. A property known as 'the body-effect' on the DMOS switch devices causes various parametric effects to occur. One of these effects is the reduction in C<sub>S(on)</sub> for an increasing V body-source. Note, however, that to increase V- normally requires V+ to be reduced (since V+ to V- = 21 V max.). Reduction in V+ causes an increase in R<sub>DS(on)</sub>, hence a compromise has to be achieved. It is also useful to note that optimum video linearity performance (e.g., differential phase and gain) occurs when V- is around - 3 V.
- 3. V- eliminates the need to bias the analog signal using potential dividers and large coupling capacitors.

#### Decoupling

It is an established RF design practice to incorporate sufficient bypass capacitors in the circuit to decouple the power supplies to all active devices in the circuit. The dynamic performance of the DG54X is adversely affected by poor decoupling of power supply pins. Also, of even more significance, since the substrate of the device is connected to the negative supply, adequate decoupling of this pin is essential.

#### **Rules:**

- 1. Decoupling capacitors should be incorporated on all power supply pins (V+, V-). (See Figure 7.)
- 2. They should be mounted as close as possible to the device pins.
- 3. Capacitors should have good high frequency characteristics - tantalum bead and/or monolithic ceramic types are adequate. Suitable decoupling capacitors are 1- to 10 µF tantalum bead, plus 10- to 100 nF ceramic.



DG540, DG541, DG542

Vishay Siliconix

Figure 7. Supply Decoupling

- 3 \

#### **Board Layout**

 $C_1 = 10 \ \mu F$  Tantalum

C<sub>2</sub> = 0.1 µF Ceramic

PCB layout rules for good high frequency performance must be observed to achieve the performance boasted by the DG540. Some tips for minimizing stray effects are:

- 1. Use extensive ground planes on double sided PCB, separating adjacent signal paths. Multilayer PCB is even better.
- 2. Keep signal paths as short as practically possible, with all channel paths of near equal length.
- 3. Careful arrangement of ground connections is also very important. Star connected system grounds eliminate signal current flowing through ground path parasitic resistance from coupling between channels.

**Vishay Siliconix** 

#### **APPLICATIONS**

Figure 8 shows a 4 Channel video multiplexer using a DG540.

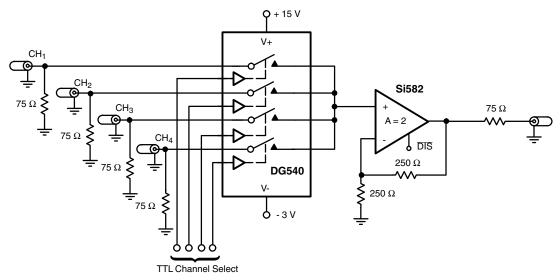




Figure 9 shows an RGB selector switch using two DG542s.

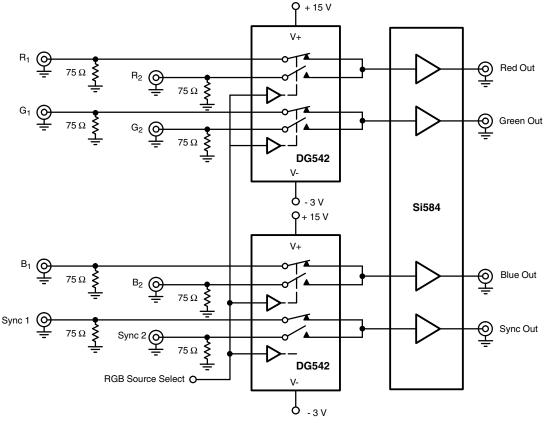


Figure 9. RGB Selector Using Two DG542s

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg?70055">www.vishay.com/ppg?70055</a>.

www.vishay.com 10





SOIC (NARROW): 16-LEAD

JEDEC Part Number: MS-012







#### PDIP: 16-LEAD





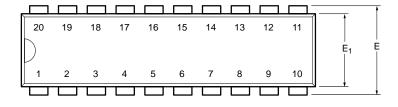


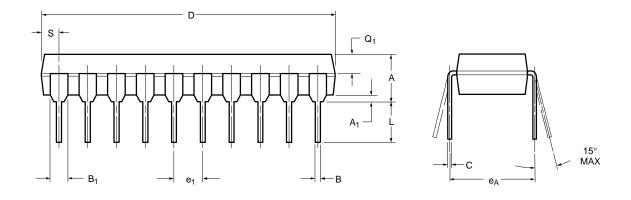
	MILLIN	IETERS	INC	ICHES		
Dim	Min	Max	Min	Max		
Α	3.81	5.08	0.150	0.200		
A <sub>1</sub>	0.38	1.27	0.015	0.050		
В	0.38	0.51	0.015	0.020		
B <sub>1</sub>	0.89	1.65	0.035	0.065		
С	0.20	0.30	0.008	0.012		
D	18.93	21.33	0.745	0.840		
E	7.62	8.26	0.300	0.325		
E <sub>1</sub>	5.59	7.11	0.220	0.280		
<b>e</b> <sub>1</sub>	2.29	2.79	0.090	0.110		
e <sub>A</sub>	7.37	7.87	0.290	0.310		
L	2.79	3.81	0.110	0.150		
Q <sub>1</sub>	1.27	2.03	0.050	0.080		
S	0.38	1.52	.015	0.060		
	ECN: S-03946—Rev. D, 09-Jul-01 DWG: 5482					



# Package Information Vishay Siliconix

#### PDIP: 20-LEAD



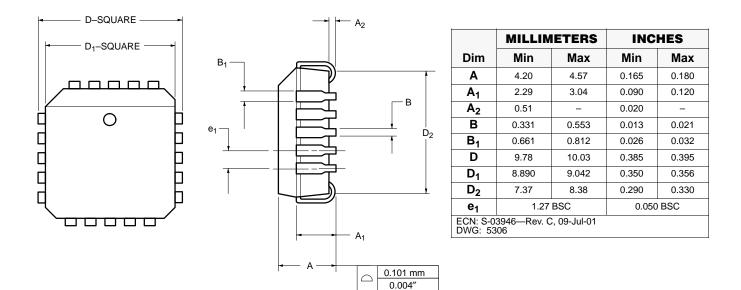


	MILLIN	<b>IETERS</b>	INC	HES	
Dim	Min	Max	Min	Max	
Α	3.81	5.08	0.150	0.200	
A <sub>1</sub>	0.38	1.27	0.015	0.050	
В	0.38	0.51	0.015	0.020	
B <sub>1</sub>	0.89	1.65	0.035	0.065	
С	0.20	0.30	0.008	0.012	
D	24.89	26.92	0.980	1.060	
Е	7.62	8.26	0.300	0.325	
E <sub>1</sub>	5.59	7.11	0.220	0.280	
<b>e</b> <sub>1</sub>	2.29	2.79	0.090	0.110	
e <sub>A</sub>	7.37	7.87	0.290	0.310	
L	3.175	3.81	0.123	0.150	
<b>Q</b> 1	1.27	2.03	0.050	0.080	
S	1.02	2.03	0.040	0.080	
ECN: S-03946—Rev. B, 09-Jul-01 DWG: 5484					



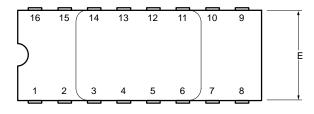
### Package Information Vishay Siliconix

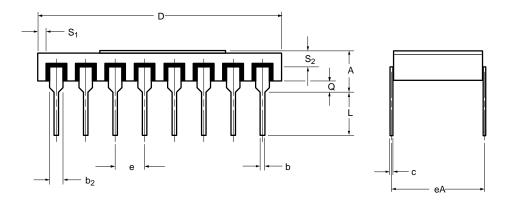
#### PLCC: 20-LEAD





#### SIDEBRAZE: 16-LEAD

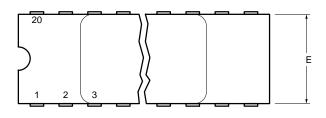


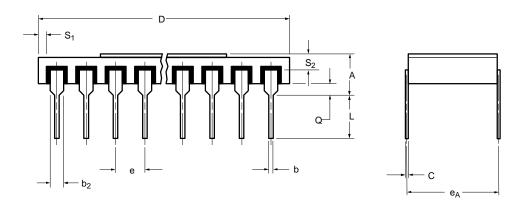


	MILLIM	IETERS	INC	HES		
Dim	Min	Max	Min	Max		
Α	2.67	4.45	0.105	0.175		
b	0.38	0.53	0.015	0.021		
b <sub>2</sub>	1.14	1.65	0.045	0.065		
С	0.20	0.30	0.008	0.012		
D	19.56	21.08	0.770	0.830		
E	7.11	7.87	0.280	0.310		
е	2.54	BSC	0.100	BSC		
e <sub>A</sub>	7.62	BSC	0.300	BSC		
L	3.18	4.45	0.125	0.175		
Q	0.64	1.40	0.025	0.055		
S <sub>2</sub>	0.25	-	0.010	-		
S <sub>1</sub>	0.13	-	0.005	-		
	ECN: S-03946—Rev. G, 09-Jul-01 DWG: 5418					



SIDEBRAZE: 20-LEAD Meets MIL-STD-1835, D8, Configuration C





	MILLIM	IETERS	INC	HES		
Dim	Min	Max	Min	Max		
Α	2.67	4.45	0.105	0.175		
b	0.38	0.53	0.015	0.021		
b <sub>2</sub>	1.14	1.65	0.045	0.065		
С	0.20	0.30	0.008	0.012		
D	24.89	26.16	0.980	1.030		
E	7.11	7.87	0.280	0.310		
е	2.54 BSC 0.100 BSC					
e <sub>A</sub>	7.62	BSC	0.300	BSC		
L	3.18	4.45	0.125	0.175		
Q	0.64	1.40	0.025	0.055		
S <sub>2</sub>	0.25	-	0.010	-		
S <sub>1</sub>	0.13	-	0.005	-		
	ECN: S-03946—Rev. D, 09-Jul-01 DWG: 5309					

# **Application Note 826**

Vishay Siliconix



#### **RECOMMENDED MINIMUM PADS FOR SO-16**



Recommended Minimum Pads Dimensions in Inches/(mm)

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